Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small SMD plastic package: 1.0 × 0.6 × 0.37 mm
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance R_{DSon} = 470 m Ω

3. Applications

- · Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | 20 | V |
| V_{GS} | gate-source voltage | | | -8 | - | 8 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | - | 0.6 | Α |
| Static characteristics | | | | | , | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 4.5 \text{ V}; I_D = 0.6 \text{ A}; T_j = 25 \text{ °C}$ | | - | 470 | 620 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



20 V, N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1 | G | gate | 1 🔲 | D I |
| 2 | S | source | 2 3 | |
| 3 | D | drain | Transparent top view DFN1006B-3 (SOT883B) | G S 017aaa255 |

6. Ordering information

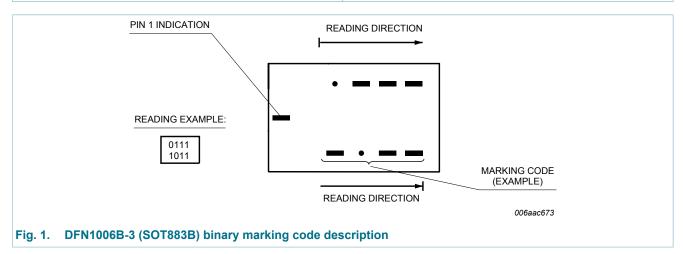
Table 3. Ordering information

| Type number | Package | | | | |
|-------------|------------|--|---------|--|--|
| | Name | Description | Version | | |
| PMZB600UNE | DFN1006B-3 | DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm | SOT883B | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMZB600UNE | 0101 1000 |



20 V, N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 20 | V |
| V_{GS} | gate-source voltage | | | -8 | 8 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | 0.6 | Α |
| | | V _{GS} = 4.5 V; T _{amb} = 100 °C | [1] | - | 0.4 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | 2.5 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 360 | mW |
| | | | [1] | - | 715 | mW |
| | | T _{sp} = 25 °C | | - | 2700 | mW |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-dra | in diode | | | - | | |
| Is | source current | T _{amb} = 25 °C | [1] | - | 0.4 | Α |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

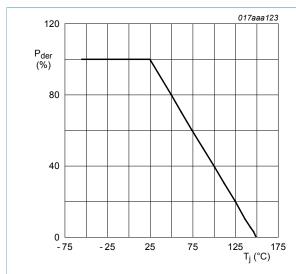


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

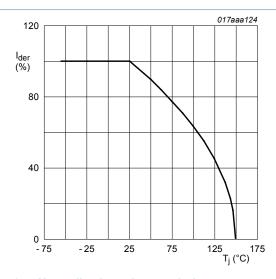


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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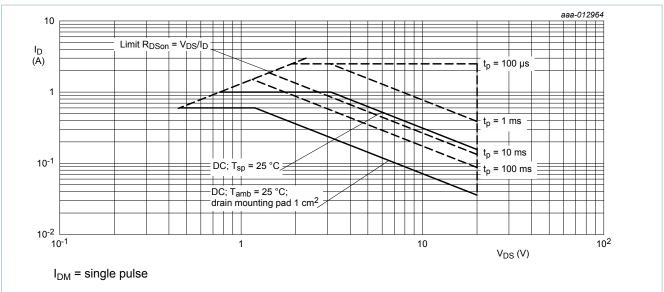


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| from jur | thermal resistance | junction to | [1] | - | 305 | 360 | K/W |
| | from junction to ambient | | [2] | - | 150 | 175 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 40 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

20 V, N-channel Trench MOSFET

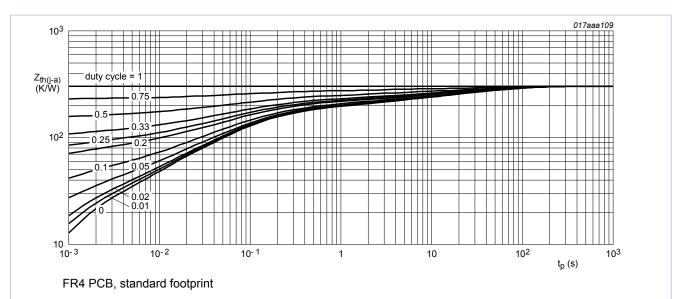


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

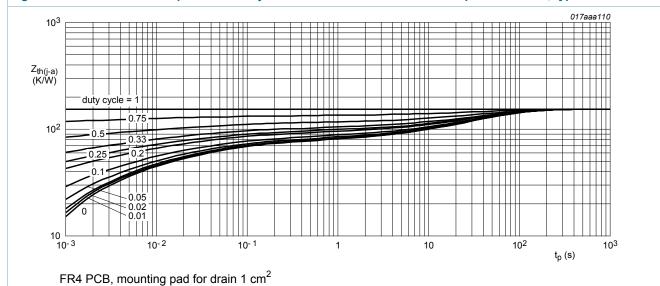


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|--|------|------|------|------|
| Static cha | racteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 0.45 | 0.7 | 0.95 | V |
| I _{DSS} | drain leakage current | V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μA |
| | | V _{DS} = 20 V; V _{GS} = 0 V; T _j = 150 °C | - | - | 10 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μA |
| | | V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -10 | μA |
| | | V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 1 | μA |
| | | $V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | - | -1 | μA |
| R _{DSon} | Son drain-source on-state | V_{GS} = 4.5 V; I_D = 0.6 A; T_j = 25 °C | - | 470 | 620 | mΩ |
| | resistance | V _{GS} = 4.5 V; I _D = 0.6 A; T _j = 150 °C | - | 760 | 1000 | mΩ |
| | | V_{GS} = 2.5 V; I_D = 0.5 A; T_j = 25 °C | - | 620 | 850 | mΩ |
| | | V_{GS} = 1.8 V; I_D = 0.1 A; T_j = 25 °C | - | 845 | 1300 | mΩ |
| | | V_{GS} = 1.5 V; I_D = 10 mA; T_j = 25 °C | - | 1125 | 3000 | mΩ |
| | | V_{GS} = 1.2 V; I_D = 1 mA; T_j = 25 °C | - | 2210 | - | mΩ |
| 9 _{fs} | forward transconductance | $V_{DS} = 5 \text{ V}; I_D = 0.6 \text{ A}; T_j = 25 \text{ °C}$ | - | 1 | - | S |
| R_G | gate resistance | f = 1 MHz | - | 34 | - | Ω |
| Dynamic o | characteristics | | , | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = 10 V; I _D = 0.6 A; V _{GS} = 4.5 V; | - | 0.4 | 0.7 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 0.1 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.1 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V; | - | 21.3 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 5.4 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 4.2 | - | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = 10 V; I _D = 0.6 A; V _{GS} = 4.5 V; | - | 5.6 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 9.2 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 19 | - | ns |
| t _f | fall time | | - | 51 | - | ns |

20 V, N-channel Trench MOSFET

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------|----------------------|---|--|-----|-----|-----|------|
| Source-drain o | Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 0.36 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | | - | 8.0 | 1.2 | V |

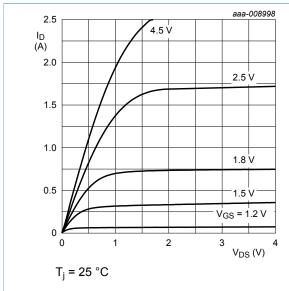


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

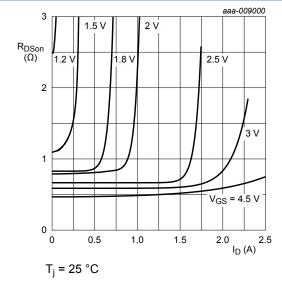


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

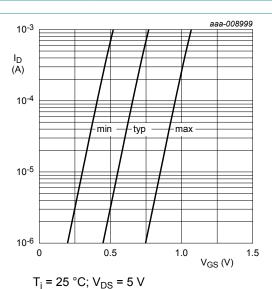


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

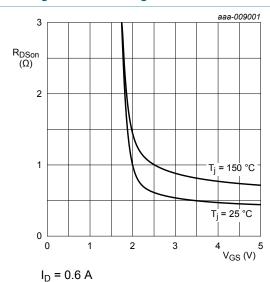


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

20 V, N-channel Trench MOSFET

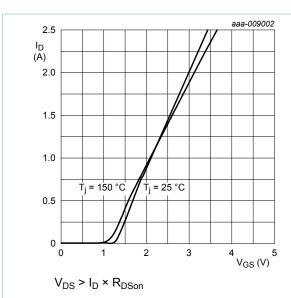


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

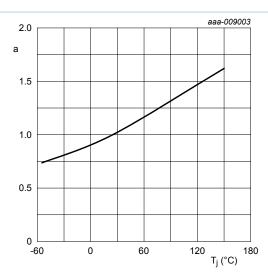


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

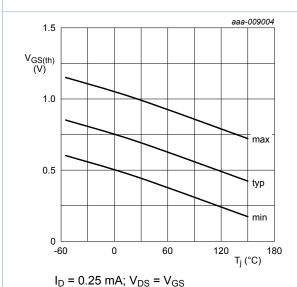
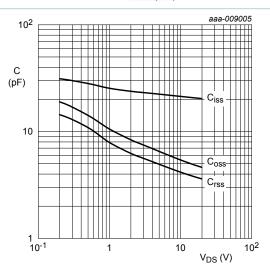


Fig. 13. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; V_{GS} = 0 V

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

20 V, N-channel Trench MOSFET

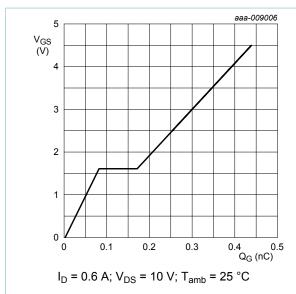


Fig. 15. Gate-source voltage as a function of gate charge; typical values

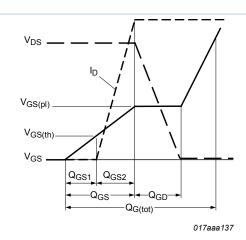


Fig. 16. MOSFET transistor: Gate charge waveform definitions

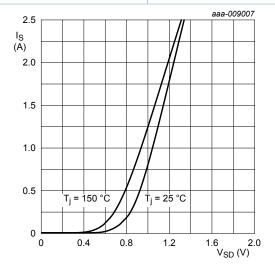
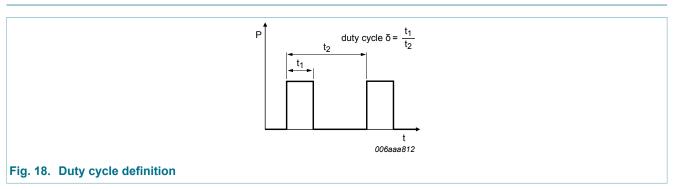


Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



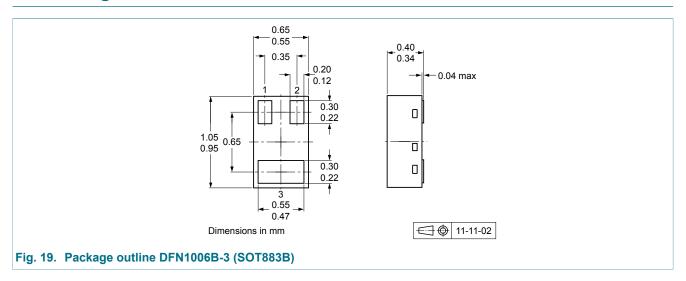
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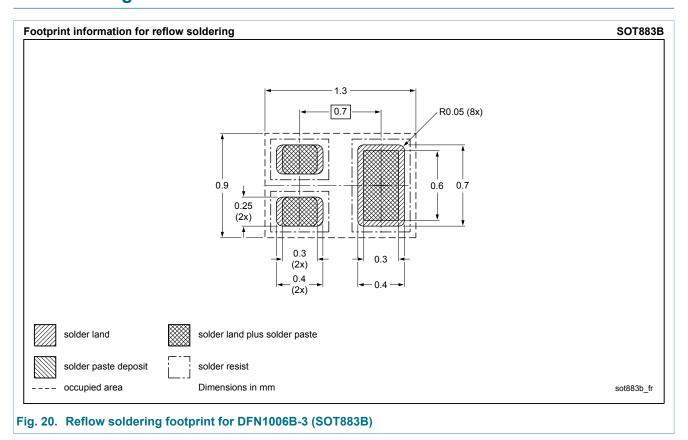
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20 V, N-channel Trench MOSFET

12. Package outline



13. Soldering



20 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMZB600UNE v.1 | 20140721 | Product data sheet | - | - |

20 V, N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
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| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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20 V, N-channel Trench MOSFET

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20 V, N-channel Trench MOSFET

16. Contents

| 1 | General description | 1 |
|------|-------------------------|----|
| 2 | Features and benefits | 1 |
| 3 | Applications | 1 |
| 4 | Quick reference data | 1 |
| 5 | Pinning information | 2 |
| 6 | Ordering information | 2 |
| 7 | Marking | 2 |
| 8 | Limiting values | 3 |
| 9 | Thermal characteristics | 4 |
| 10 | Characteristics | 6 |
| 11 | Test information | 9 |
| 12 | Package outline | 10 |
| 13 | Soldering | 10 |
| 14 | Revision history | 11 |
| 15 | Legal information | 12 |
| 15.1 | Data sheet status | 12 |
| 15.2 | Definitions | 12 |
| 15.3 | Disclaimers | 12 |
| 15.4 | Trademarks | 13 |
| | | |

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